## KW102103/879.1.004.IDS

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Applicant

Kin P. Cheung

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Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

## <u>INFORMATION DISCLOSURE STATEMENT</u>

Dear Sir:

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Transmitted herewith is an Information Disclosure Statement ("IDS") in the abovereferenced Application, together with a Form-1449 listing all references cited and a copy of each reference.

## KW102103/879.1.004.IDS

This IDS is being mailed within three (3) months of filing of the above-captioned Application, if it is a National Application, or within three (3) months of entering, as set forth in 37 C.F.R. § 1.491, the national stage of the above-captioned Application, if the above-captioned Application is an International Application. Therefore, consideration of the IDS by the Patent and Trademark Office, without the payment of any additional fee, is believed to be due under 37 C.F.R. § 1.97(b). However, the Commissioner is hereby authorized to charge Deposit Account No. 23-0510 if any fee under 37 C.F.R. 1.17 is deemed necessary for the accompanying references to be considered by the Patent and Trademark Office

All the references are in English and/or are cited in an accompanying English language version of the Search Report by another Patent Office, so that comment on the references by the Applicant is not required under 37 C.F.R. § 1.98(a).

Respectfully submitted,

Kenneth Watov, Esq. Registration No. 26,042

Attorney for Applicant

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ADDRESS ALL CORRESPONDENCE TO: Kenneth Watov, Esq. WATOV & KIPNES, P.C. P.O. Box 247 Princeton Junction, NJ 08550 (609)243-0330 8791004.Form-PTO-1449 Sheet of

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